

#### Precision Micropower Shunt Voltage Reference in bare die form

Rev 1.1 29/07/22

#### Description

The LM4040D-2.5 is a high precision, two-terminal shunt mode, bandgap voltage reference with fixed reverse breakdown voltage of 2.5V. The device is ideal for space-critical high reliability applications with initial 1% accuracy and 150ppm/°C max temperature coefficient. A 65µA to 15mA shunt current capability with low dynamic impedance ensures stable reverse breakdown voltage accuracy over a wide current range and operating temperature. No external stabilizing capacitors are required.

### **Ordering Information**

The following part suffixes apply:

- No suffix MIL-STD-883 /2010B Visual Inspection
- "H" MIL-STD-883 /2010B Visual Inspection
   + MIL-PRF-38534 Class H LAT
- "K" MIL-STD-883 /2010A Visual Inspection (Space)
   + MIL-PRF-38534 Class K\_AT

LAT = Lot Acceptance Test.

For further information on LAT places flows see below.

www.siliconsupplies.com\quality\bare-die-lot-qualification

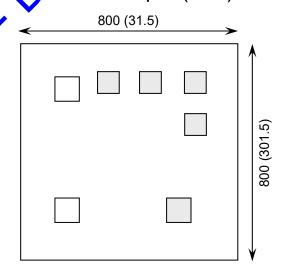
### Supply Formats:

- Defaut Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 280µm(11 Mils) On request
- In Metal or Ceramic package On request

#### Features:

- ±1% (max) output voltage tolerance >1/25°C
- 15ppm/°C typical temperature coefficient at 25°C
- Wide operating current range CS A to 15mA
- No output capacitor required
- Tolerates capacitive local
- Bandgap reference corrects temperature drift
- Specified over military temperature range.

#### Die Qimensions in µm (mils)



### **Mechanical Specification**

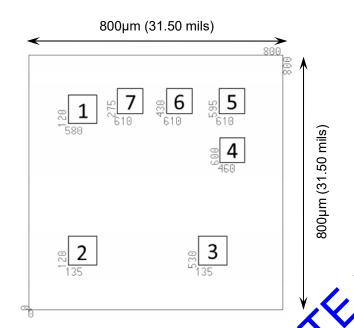
Die Size (Unsawn)	800 x 800 31.5 x 31.5	μm mils	
Minimum Bond Pad Size	90 x 90 3.54 x 3.54	μm mils	
Die Thickness	260 (±20) 10.24 (±0.8)	μm mils	
Top Metal Composition	Al 1%Si 1.4µm		
Back Metal Composition	Ti/Ni/Ag 1.2µm		





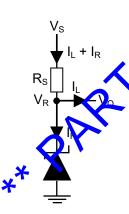
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### Pad Layout and Functions



PAD	FUNCTION	CCOPLIN	NATES (µm)		
ו אם	I SHOTION	/ Y	Y		
1	CATHODE +	120	580		
2	ANODE -	120	135		
3	NO COLINECT	530	135		
4	NC CONNECT	600	480		
5	NOCONNECT	595	610		
0	NO CONNECT	430	610		
	NO CONNECT	275	610		
CONNECT CHIP BACK TO GND					

## **Typical Application**



An external series resistor ( $R_S$ ) is connected between the supply voltage,  $V_S$ , and the LIM 0.10 I0.

 $R_S$  determines the current that flows through the load ( $I_L$ ) and the LM4040D ( $I_R$ ). Since load current and supply voltage may vary,  $R_S$  should be small enough to supply at least the minimum acceptable  $I_R$  to the LM4040D even when the supply voltage is at its minimum and the load current is at its maximum value. When the supply voltage is at its maximum and  $I_L$  is at its minimum,  $R_S$  should be large enough so that the current flowing through the LM4040D is less than 15mA.

 $R_{\rm S}$  is determined by the supply voltage, (V<sub>S</sub>), the load and operating current, (I<sub>L</sub> and I<sub>R</sub>), and the LM4040D's reverse breakdown voltage, V<sub>R</sub>.

$$R_S = \frac{V_S - V_R}{I_I + I_R}$$





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## Absolute Maximum Ratings<sup>1</sup> T<sub>A</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIZ
Reverse Current	I <sub>R</sub>	25	MΑ
Forward Current	I <sub>F</sub>	10	n.A
Operating Temperature Range	TJ	-55 to 150	C
Storage Temperature	T <sub>STG</sub>	-65 to 150	°C

<sup>1.</sup> Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, to extended periods, may reduce device reliability.

## Recommended Operating Conditions T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	MIN	MAX	UNIT
Reverse Current	I <sub>R</sub>	0.065	15	mA
Operating Temperature Range	-	-55 to	125	°C

#### Electrical Characteristics, T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Reverse Breakdown Voltage	V <sub>R</sub>	I <sub>R</sub> =100μ <b>Α</b>	-	2.5	-	V
Reverse Breakdown Voltage Tolerance <sup>2</sup>	V <sub>R</sub>	I <sub>R</sub> ₹100μA	-	-	±25	mV
		$I_R = 100 \mu A$ , $T_J = -40 \text{ to } 85^{\circ}\text{C}$	-	-	±49	
		I <sub>R</sub> =10° (A T <sub>J</sub> = -55 to 125°C	-	-	±63	
Minimum On a matina		T <sub>J</sub> = 25°C	-	45	65	μA
Minimum Operating Current	I <sub>RMIN</sub>	$T_{\rm J}$ = -40 to 85°C	-	-	70	
Guirone		T <sub>J</sub> = -55 to 125°C	-	-	73	
	ΔV <sub>R</sub> / ΔT	I <sub>R</sub> =10mA	-	±20	-	ppm /°C
Average Reverse Breakdown Voltage Temperature Coefficient <sup>2</sup>		I <sub>R</sub> =1mA	-	±15	-	
		I <sub>R</sub> =100μA	-	±15	-	
		I <sub>R</sub> =10mA, T <sub>J</sub> = -55 to 125°C	-	-	±150	
		$I_R = 1 \text{mA}, T_J = -55 \text{ to } 125^{\circ}\text{C}$	-	-	±150	
		$I_R = 100 \mu A$ , $T_J = -55 \text{ to } 125 ^{\circ}\text{C}$	-	-	±150	
Breakdown Voltage Change with Operating Current Change <sup>7</sup>	$\Delta V_R / \Delta I_R$	$I_{RMIN} \le I_R \le 1mA$	-	0.3	1	
		$I_{RMIN} \le I_R \le 1 \text{mA}, T_J = -55 \text{ to } 125^{\circ}\text{C}$	-	-	1.2	mV
		1mA ≤ I <sub>R</sub> ≤ 15mA	-	2.5	8	1110
		$1 \text{mA} \le I_R \le 15 \text{mA}, T_J = -55 \text{ to } 125 ^{\circ}\text{C}$	-	-	10	



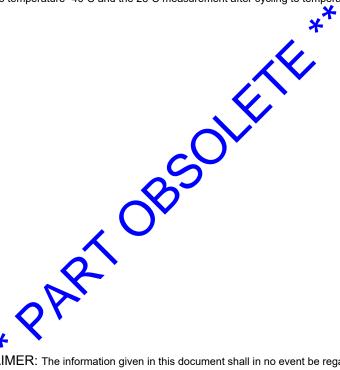


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#### Electrical Characteristics, T, = 25°C unless otherwise stated

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Reverse Dynamic Impedance	Z <sub>R</sub>	I <sub>R</sub> = 1mA, f = 120 Hz, I <sub>AC</sub> = 0.1 I <sub>R</sub>	-	0.3	1.1	Ω
Wideband Noise	e <sub>N</sub>	I <sub>R</sub> =100μA, 10 Hz ≤ f ≤ 10 kHz	-	35	1	$\mu V_{RMS}$
Reverse Breakdown Voltage Long Term Stability	$\Delta V_R$	t = 1000 hours T = 25°C ±0.1°C, I <sub>R</sub> =100μA	-	120	-	ppm
Thermal Hysteresis	V <sub>HYST</sub>	ΔT = -40 to 125°C	6	0.08	-	%

2. Reverse Breakdown Tolerance is defined as the room temperature Reverse Breakdown Votage olerance  $\pm [(\Delta V_R/\Delta T)(max\Delta T)(V_R)]$ . Where,  $\Delta V_R/\Delta T$  is the  $V_R$  temperature coefficient,  $max\Delta T$  is the maximum difference in temperature from the reference point of 25°C to  $T_{MIN}$  or  $T_{MAX}$ , and  $V_R$  is the reverse breakdown voltage. 3. Load regulation is measured on pulse basis from no load to the specified load current. Output changes due to die temperature change must be taken into account separately. Thermal hysteresis is defined as the difference in voltage measured at +25°C after cycling to temperature -40°C and the 25°C measurement after cycling to temperature +125°C.



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